MJD32C

Rev.E May.-2016

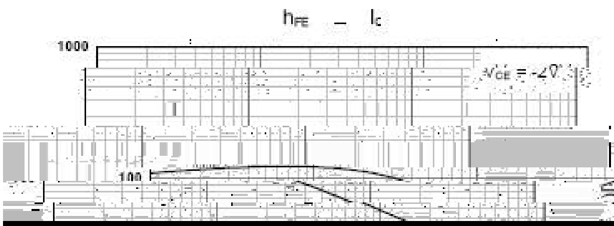
TO-252 PNP Silicon PNP transistor in a TO-252 Plastic Package.

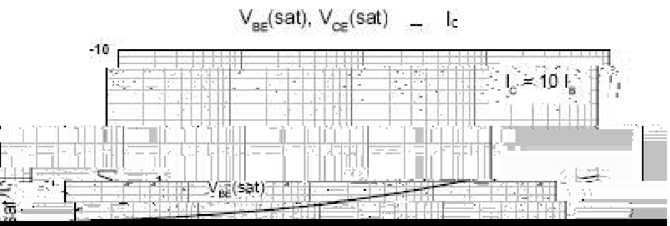
Low Speed ,Load Formed for Surface Mount Application.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-3.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-5.0	A
Base Current - Continuous	I_B	-1.0	A
Collector Power Dissipation	P_C(T_C=25)	15	W
Collector Power Dissipation	P		

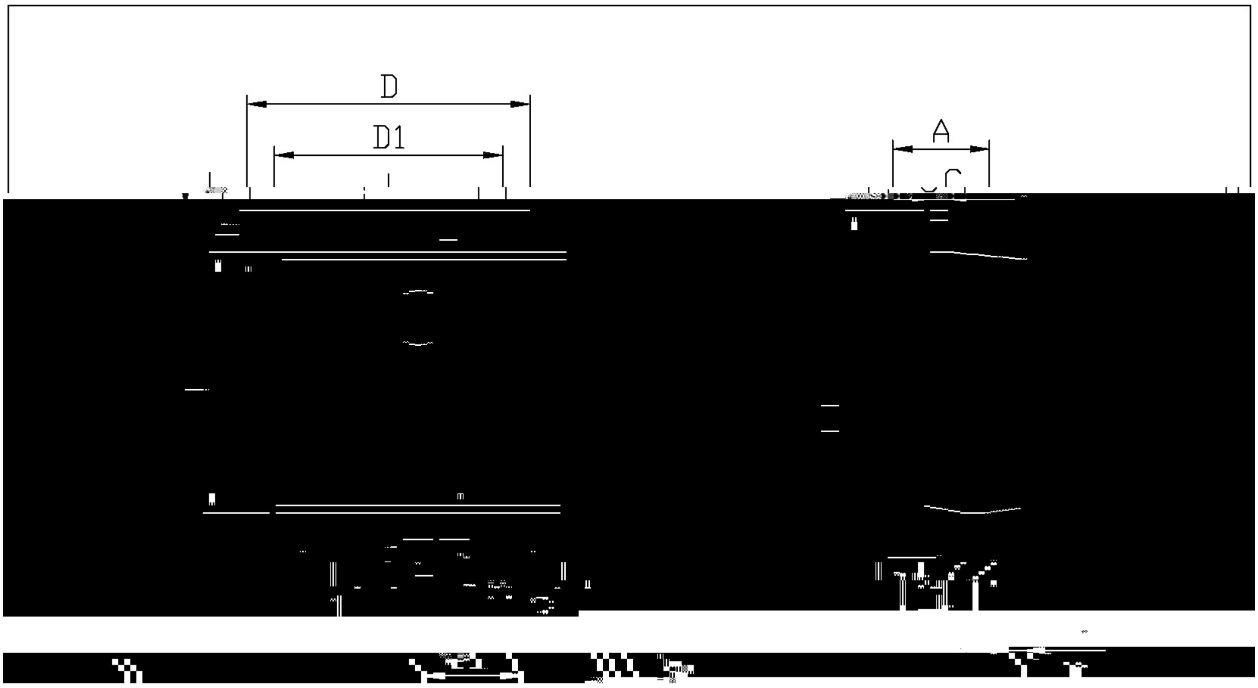
C

/ Electrical Characteristic Curve





/ Package Dimensions

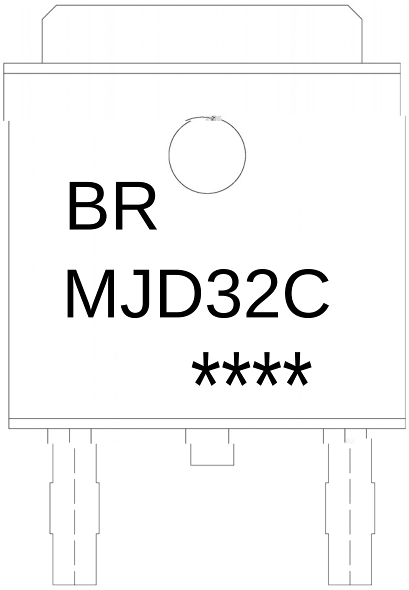


00	0.10

D1	5.10	5.50	K	0.

TO-252

/ Marking Instructions



BR

MJD32C

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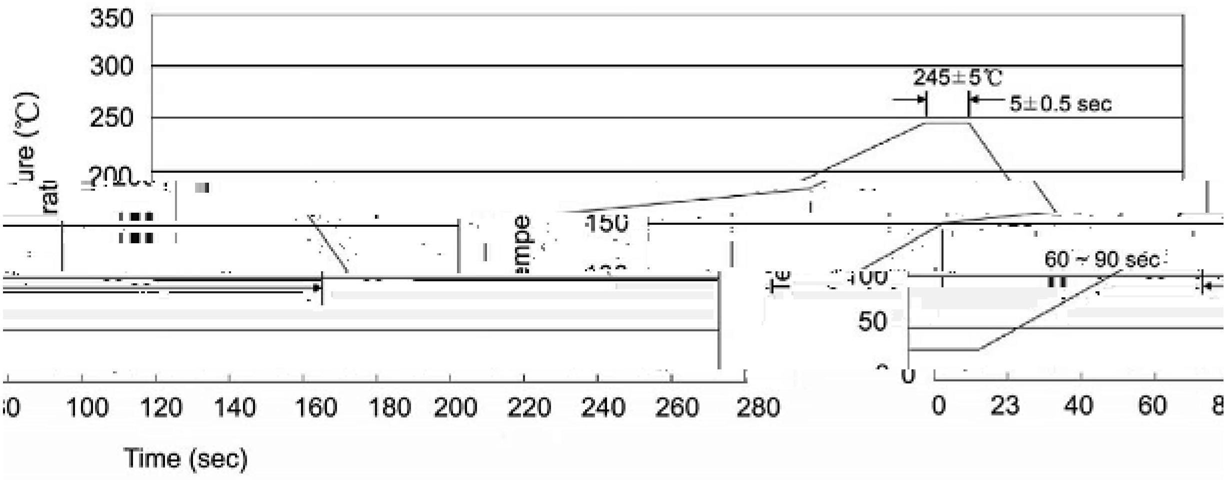
Note:

BR:	Company Code
MJD32C:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

1 25 150 60 90sec;
1.Preheating:25~150 , Time:60~90sec.

2 245±5 5±0.5sec;
2.Peak Temp.:245±5 , Duration:5±0.5sec.

3 2 10 /sec.
3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

260±5 10±1 sec. Temp.:260±5 Time:10±1 sec

/ Packaging SPEC.

/ REEL

Package Type	Units			Dimension (unit mm^3)
	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	